

2SB1190, 2SB1190A

Silicon PNP Epitaxial Planar Type

Power Amplifier

TV Vertical Deflection Output

Complementary Pair with 2SD1770, 2SD1770A

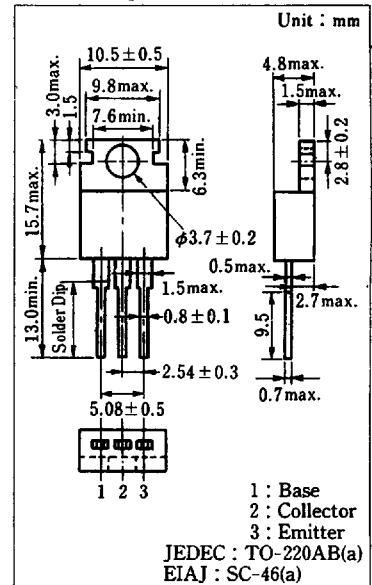
■ Features

- High collector-emitter voltage (V_{CE0})
- Large collector power dissipation (P_C)

■ Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Item	Symbol	Value	Unit
Collector-base voltage	2SB1190	-200	V
	2SB1190A	-200	
Collector-emitter voltage	2SB1190	-150	V
	2SB1190A	-180	
Emitter-base voltage	V_{EBO}	-6	V
Peak collector current	I_{CP}	-2	A
Collector current	I_C	-1	A
Collector power dissipation	$T_c=25^\circ\text{C}$	25	W
	$T_a=25^\circ\text{C}$	1.4	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	$-55 \sim +150$	$^\circ\text{C}$

■ Package Dimensions



■ Electrical Characteristics ($T_c=25^\circ\text{C}$)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CB0}	$V_{CB} = -200, I_E = 0$			-50	μA
Emitter cutoff current	I_{EB0}	$V_{EB} = -4 \text{ V}, I_C = 0$			-50	μA
Collector-emitter voltage	2SB1190 2SB1190A	V_{CEO} $I_C = -5 \text{ mA}, I_B = 0$	-150			V
			-180			
Emitter-base voltage	V_{EBO}	$I_E = -0.5 \text{ mA}, I_C = 0$	-6			V
DC current gain	h_{FE1}^*	$V_{CE} = -10 \text{ V}, I_C = -100 \text{ mA}$	60		240	
	h_{FE2}	$V_{CE} = -10 \text{ V}, I_C = -300 \text{ mA}$	50			
Base-emitter voltage	V_{BE}	$V_{CE} = -10 \text{ V}, I_C = -300 \text{ mA}$			-1	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$			-1	V
Transition frequency	f_T	$V_{CE} = -10 \text{ V}, I_C = -100 \text{ mA}, f = 1 \text{ MHz}$		20		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		35		pF

* h_{FE1} Classifications

Class	Q	P
h_{FE}	60 ~ 140	100 ~ 240

6932852 0016258 956

